Silicon PNP Power Transistors 2N6420

DESCRIPTION

- With TO-66 package
- Continuous collector current-I_C=-1A
- Power dissipation -PD=35W @T_C=25℃
- Complement to type 2N3583

APPLICATIONS

- High speed switching and linear amplifier
- High-voltage operational amplifiers
- Switching regulators ,converters
- Deflection stages and high fidelity amplifers

Fig.1 simplified outline (TO-66) and symbol

PINNING (See Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

Absolute maximum ratings(Ta=25℃)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-250	V
V_{CEO}	Collector-emitter voltage	Open base	-175	V
V_{EBO}	Emitter-base voltage	Open collector	-6	V
I_C	Collector current		-1.0	A
I_{CM}	Collector current-Peak		-5.0	A
I_B	Base current		-1.0	A
P_T	Total power dissipation	T_C=25℃	35	W
T_j	Junction temperature		200	℃
T_{stg}	Storage temperature		-65~200	℃

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j\text{-}C}$	Thermal resistance junction to case	5.0	℃/W

Silicon PNP Power Transistors 2N6420

CHARACTERISTICS

Tj=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-emitter sustaining voltage	I_C=-50mA ; I_B=0	-175			V
V_{CEsat}	Collector-emitter saturation voltage	I_C=-1A; I_B=-0.125A			-5.0	V
V_{BE}	Base -emitter on voltage	I_C=-1A ; V_{CE}=-10V			-1.4	V
I_{CEX}	Collector cut-off current	V_{CE}=-225V;$V_{BE(off)}$=-1.5V T_C=150℃			-1.0 -3.0	mA
I_{CEO}	Collector cut-off current	V_{CE}=-150V I_B=0			-10	mA
I_{EBO}	Emitter cut-off current	V_{EB}=-6V; I_C=0			-5.0	mA
h_{FE-1}	DC current gain	I_C=-0.1A ; V_{CE}=-10V	40			
h_{FE-2}	DC current gain	I_C=-0.5A ; V_{CE}=-10V	40		200	
h_{FE-3}	DC current gain	I_C=-1A ; V_{CE}=-10V	10			

PACKAGE OUTLINE

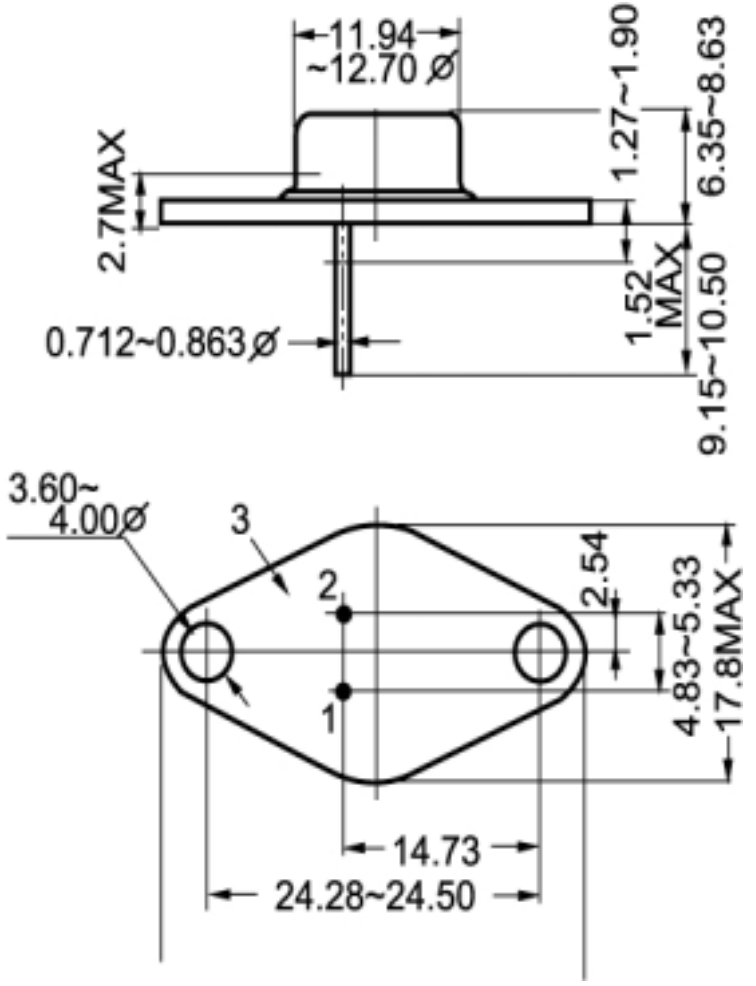

Fig.2 Outline dimensions